

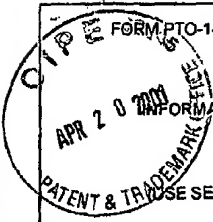


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| FORM PTO-1449<br>U.S. DEPARTMENT OF COMMERCE<br>PATENT AND TRADEMARK OFFICE<br>INFORMATION DISCLOSURE STATEMENT<br>BY APPLICANT<br>(SEE SEVERAL SHEETS IF NECESSARY) | ATTY. DOCKET NO.<br>ASMJP.065AUS   | APPLICATION NO.<br>09/779,397 |
|  | RECEIVED<br>APR 23 2001<br>GROUP<br>Unknown 1762                           |                               |
|  | APPLICANT<br>Michael A. Todd<br>FILING DATE<br>February 7, 2001<br>TC 1700 |                               |

| U.S. PATENT DOCUMENTS |     |                 |          |                   |       |          |                                 |
|-----------------------|-----|-----------------|----------|-------------------|-------|----------|---------------------------------|
| EXAMINER<br>INITIAL   |     | DOCUMENT NUMBER | DATE     | NAME              | CLASS | SUBCLASS | FILING DATE<br>(IF APPROPRIATE) |
| B                     | 1.  | 4,781,942       | 11/01/88 | Leyden et al.     |       |          |                                 |
|                       | 2.  | 4,863,755       | 09/05/89 | Hess et al.       |       |          |                                 |
|                       | 3.  | 4,894,352       | 01/16/90 | Lane et al.       |       |          |                                 |
|                       | 4.  | 4,992,306       | 02/12/91 | Hochberg et al.   |       |          |                                 |
|                       | 5.  | 5,011,706       | 04/30/91 | Tarhay et al.     |       |          |                                 |
|                       | 6.  | 5,028,566       | 07/02/91 | Legendijk         |       |          |                                 |
|                       | 7.  | 5,231,058       | 07/27/93 | Maeda et al.      |       |          |                                 |
|                       | 8.  | 5,240,813       | 08/31/93 | Watanabe et al.   |       |          |                                 |
|                       | 9.  | 5,314,724       | 05/24/94 | Tsukune et al.    |       |          |                                 |
|                       | 10. | 5,324,539       | 06/28/94 | Maeda et al.      |       |          |                                 |
|                       | 11. | 5,380,555       | 01/10/95 | Mine et al.       |       |          |                                 |
|                       | 12. | 5,433,786       | 07/18/95 | Hu et al.         |       |          |                                 |
|                       | 13. | 5,494,712       | 02/27/96 | Hu et al.         |       |          |                                 |
|                       | 14. | 5,554,570       | 09/10/96 | Maeda et al.      |       |          |                                 |
|                       | 15. | 5,563,105       | 10/08/96 | Dobuzinsky et al. |       |          |                                 |
|                       | 16. | 5,703,404       | 12/30/97 | Matsuura          |       |          |                                 |
|                       | 17. | 5,840,821       | 11/24/98 | Nakano et al.     |       |          |                                 |
|                       | 18. | 5,876,798       | 03/02/99 | Vassiliev         |       |          |                                 |
|                       | 19. | 5,989,998       | 11/23/99 | Sugahara et al.   |       |          |                                 |
|                       | 20. | 5,998,522       | 12/07/99 | Nakano et al.     |       |          |                                 |
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|                       | 23. | 6,051,508       | 04/18/00 | Takase et al.     |       |          |                                 |
|                       | 24. | 6,054,379       | 04/25/00 | Yau et al.        |       |          |                                 |
|                       | 25. | 6,068,884       | 05/30/00 | Rose et al.       |       |          |                                 |

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| EXAMINER | DATE CONSIDERED |
|          | 9/23/03         |

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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| FOREIGN PATENT DOCUMENTS |     |                 |          |         |       |          |             |    |
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| EXAMINER<br>INITIAL      |     | DOCUMENT NUMBER | DATE     | COUNTRY | CLASS | SUBCLASS | TRANSLATION |    |
|                          |     |                 |          |         |       |          | YES         | NO |
|                          | 26. | WO 97/40207     | 10/30/97 | PCT     |       |          | X           |    |
|                          | 27. | WO 99/55526     | 11/04/99 | PCT     |       |          | X           |    |
|                          | 28. | EPO 367 004 B1  | 12/15/93 | EPO     |       |          | X           |    |
|                          | 29. | EP 0 436 185 B1 | 03/20/96 | EPO     |       |          | X           |    |
|                          | 30. | EP 0 723 600 B1 | 07/07/99 | EPO     |       |          | X           |    |
|                          | 31. | EP 0 771 886 A1 | 05/07/97 | EPO     |       |          | X           |    |
|                          | 32. | EP 0 935 283 A2 | 08/11/99 | EPO     |       |          | X           |    |
|                          | 33. | EP 0 960 958 A2 | 12/01/99 | EPO     |       |          | X           |    |

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| <b>INFORMATION DISCLOSURE STATEMENT<br/>BY APPLICANT</b> |  |                                  |  | APPLICANT<br>Michael A. Todd    |
| (USE SEVERAL SHEETS IF NECESSARY)                        |  |                                  |  | FILING DATE<br>February 7, 2001 |

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
ASMJP.065AUSAPPLICATION NO.  
09/779,397INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

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Michael A. ToddFILING DATE  
February 7, 2001GROUP  
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## FOREIGN PATENT DOCUMENTS

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|---------------------|-----------------|------------|---------|-------|----------|-------------|----|
|                     |                 |            |         |       |          | YES         | NO |
|                     | WO 99/60621     | 11/25/1999 | PCT     |       |          |             |    |
|                     | WO 99/41423     | 08/19/1999 | PCT     |       |          |             |    |
|                     | WO 99/21706     | 05/08/1999 | PCT     |       |          |             |    |
|                     | WO 97/41592     | 11/06/1997 | PCT     |       |          |             |    |
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| EXAMINER<br>INITIAL | OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.) |   |
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|                     | A.   | PATENT ABSTRACTS OF JAPAN vol. 1998, no. 03, 27 February 1998 (1998-02-27) & JP 09 293716 A (KAWASAKI STEEL CORP), 11 November 1997 (1997-11-11) *abstract*                 |
|                     | B.   | PATENT ABSTRACTS OF JAPAN vol. 1999, no.12, 29 October 1999 (1999-10-29) & JP 11 176829 A (INNTECH CORP), 2 July 1999 (1999-07-02) *abstract*                               |
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